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           10742 SEARCH 374/CLAS
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           16190 SEARCH L1 OR L2
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           28070 SEARCH METAL OXIDE
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             252 SEARCH L4 AND L3
             161 SEARCH L5 AND (ALUMINÚM
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             (19) SEARCH L5 AND MAGNESIUM
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           38346 SEARCH MANGANESE .
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              13 SEARCH L5 AND VANADIUM
L13
              35 SEARCH L5 AND ZIRCONIUM
1.14
              16 SEARCH L6 AND L7
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              7 SEARCH L14 AND L10
              2 SEARCH L15 AND L12
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L17
              2 SEARCH L16 AND L13
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